

## High voltage fast-switching NPN power transistor

### Features

- High voltage capability
- Low spread of dynamic parameters
- Very high switching speed
- Integrated antiparallel collector-emitter diode

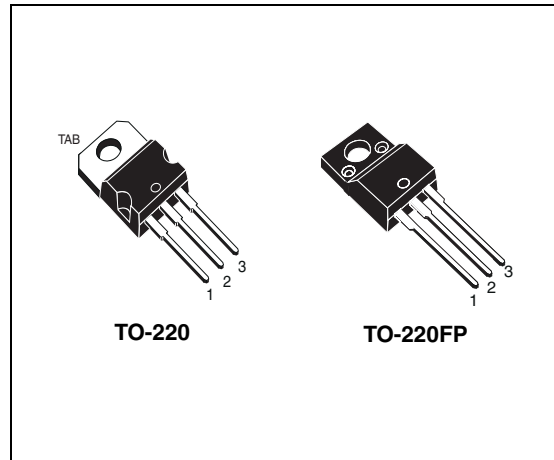
### Applications

- Electronic ballast for fluorescent lighting
- Flyback and forward single transistor low power converters

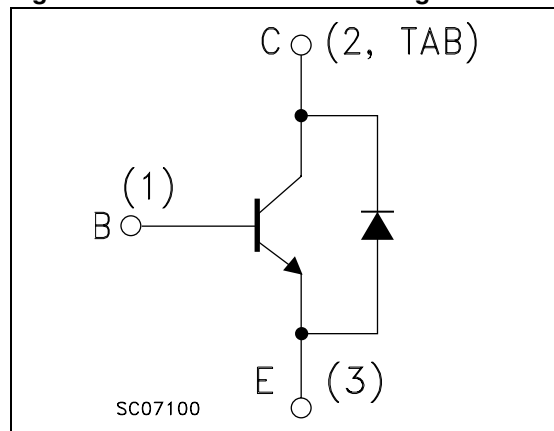
### Description

These devices are high voltage fast-switching NPN power transistors. They are manufactured using high voltage multi epitaxial planar technology for high switching speeds and medium voltage capability.

They use a cellular emitter structure with planar edge termination to enhance switching speeds while maintaining the wide RBSOA. The devices are designed for use in lighting applications and low cost switch-mode power supplies.



**Figure 1. Internal schematic diagram**



**Table 1. Device summary**

Order codes	Marking	Packages	Packaging
STL128D	L128D	TO-220	Tube
STL128DFP	L128DFP	TO-220FP	Tube

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value		Unit
		TO-220	TO-220FP	
$V_{CES}$	Collector-emitter voltage ( $V_{BE} = 0$ )	700		V
$V_{CEO}$	Collector-emitter voltage ( $I_B = 0$ )	400		V
$V_{EBO}$	Emitter-base voltage ( $I_C = 0$ )	$V_{(BR)EBO}$		V
$I_C$	Collector current	4		A
$I_{CM}$	Collector peak current ( $t_p < 5$ ms)	8		A
$I_B$	Base current	2		A
$I_{BM}$	Base peak current ( $t_p < 5$ ms)	4		A
$V_{ISOL}$	Insulation withstand voltage (RMS) from all three leads to external heatsink		1500	V
$P_{TOT}$	Total dissipation at $T_C = 25$ °C	65	30	W
$T_{stg}$	Storage temperature	-65 to 150		°C
$T_J$	Max. operating junction temperature	150		°C

**Table 3. Thermal data**

Symbol	Parameter	Value		Unit
		TO-220	TO-220FP	
$R_{thJ-case}$	Thermal resistance junction-case max	1.92	4.17	°C/W
$R_{thJ-amb}$	Thermal resistance junction-ambient max	62.5		°C/W

## 2 Electrical characteristics

$T_{\text{case}} = 25\text{ °C}$  unless otherwise specified

**Table 4. Electrical characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{\text{CES}}$	Collector cut-off current ( $V_{\text{BE}} = 0$ )	$V_{\text{CE}} = 700\text{ V}$			100	$\mu\text{A}$
		$V_{\text{CE}} = 700\text{ V}$ $T_{\text{c}} = 125\text{ °C}$			500	$\mu\text{A}$
$I_{\text{CEO}}$	Collector cut-off current ( $I_{\text{B}} = 0$ )	$V_{\text{CE}} = 400\text{ V}$			250	$\mu\text{A}$
$V_{(\text{BR})\text{EBO}}$	Emitter-base breakdown voltage ( $I_{\text{C}} = 0$ )	$I_{\text{E}} = 10\text{ mA}$	9		18	V
$V_{\text{CEO(sus)}}^{(1)}$	Collector-emitter sustaining voltage ( $I_{\text{B}} = 0$ )	$I_{\text{C}} = 100\text{ mA}$	400			V
$V_{\text{CE(sat)}}^{(1)}$	Collector-emitter saturation voltage	$I_{\text{C}} = 1\text{ A}$ $I_{\text{B}} = 0.2\text{ A}$			1	V
		$I_{\text{C}} = 2.5\text{ A}$ $I_{\text{B}} = 0.5\text{ A}$			1.5	V
		$I_{\text{C}} = 3.5\text{ A}$ $I_{\text{B}} = 0.7\text{ A}$		0.5		V
$V_{\text{BE(sat)}}^{(1)}$	Base-emitter saturation voltage	$I_{\text{C}} = 1\text{ A}$ $I_{\text{B}} = 0.2\text{ A}$			1.2	V
		$I_{\text{C}} = 2.5\text{ A}$ $I_{\text{B}} = 0.5\text{ A}$			1.3	V
$h_{\text{FE}}^{(1)}$	DC current gain	$I_{\text{C}} = 10\text{ mA}$ $V_{\text{CE}} = 5\text{ V}$	10			
		$I_{\text{C}} = 2\text{ A}$ $V_{\text{CE}} = 5\text{ V}$	10		32	
$t_{\text{s}}$ $t_{\text{f}}$	Inductive load Storage time Fall time	$V_{\text{CC}} = 200\text{ V}$ $I_{\text{C}} = 2\text{ A}$				
		$I_{\text{B1}} = 0.4\text{ A}$ $V_{\text{BE(off)}} = -5\text{ V}$ $R_{\text{BB}} = 0$ $L = 200\text{ }\mu\text{H}$		0.6		$\mu\text{s}$
				0.1		$\mu\text{s}$

1. Pulse test: pulse duration  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 1.5\%$ .

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

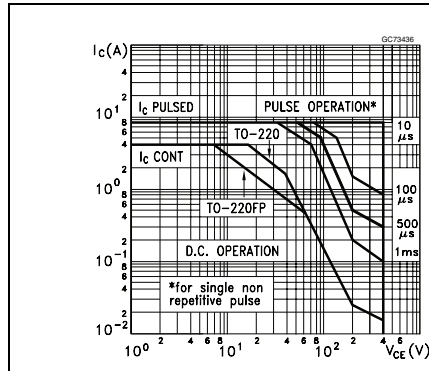


Figure 3. Derating curve

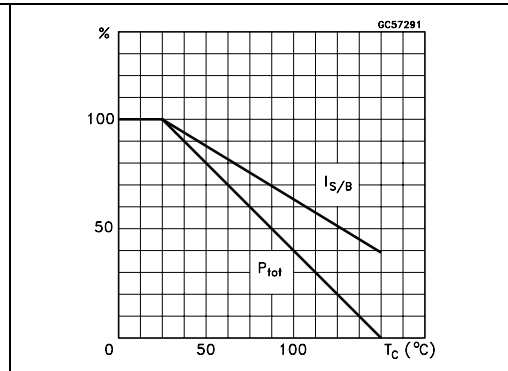


Figure 4. DC current gain ( $V_{CE} = 1.5$  V)

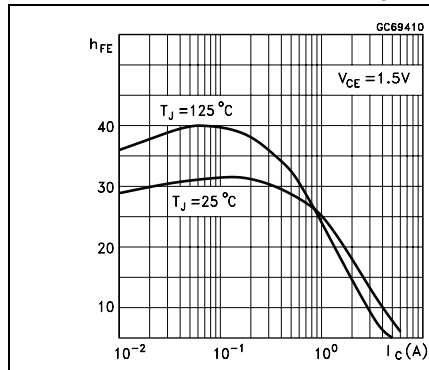


Figure 5. DC current gain ( $V_{CE} = 5$  V)

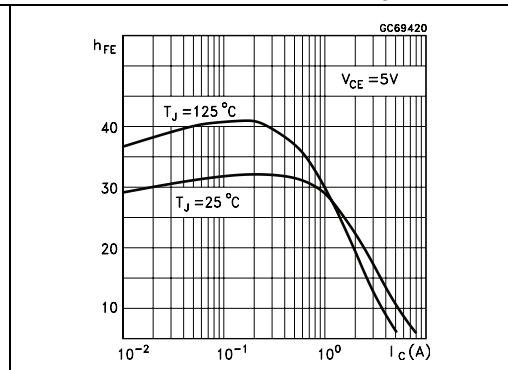


Figure 6. Collector-emitter saturation voltage

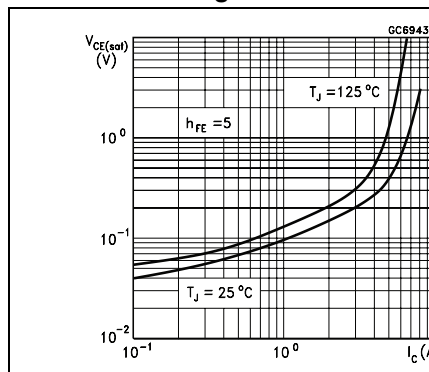
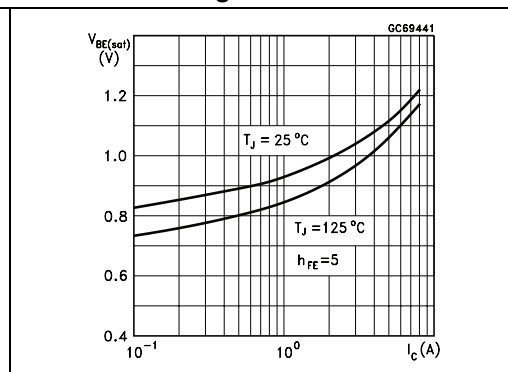
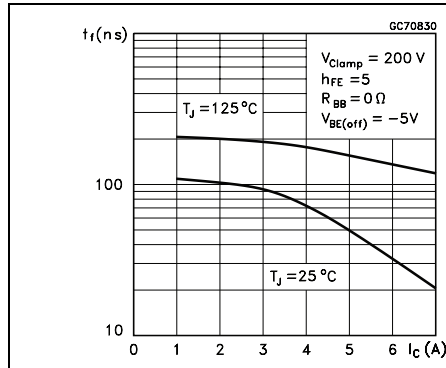


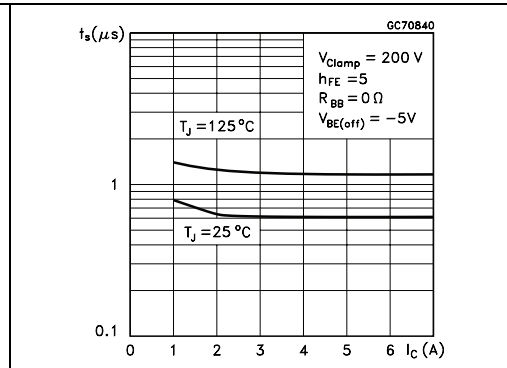
Figure 7. Base-emitter saturation voltage



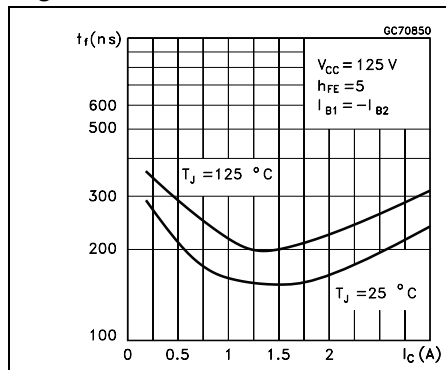
**Figure 8. Inductive load fall time**



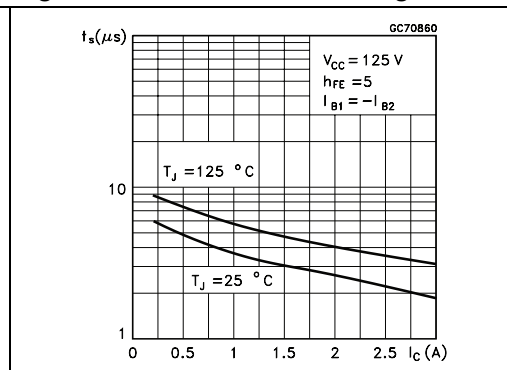
**Figure 9. Inductive load storage time**



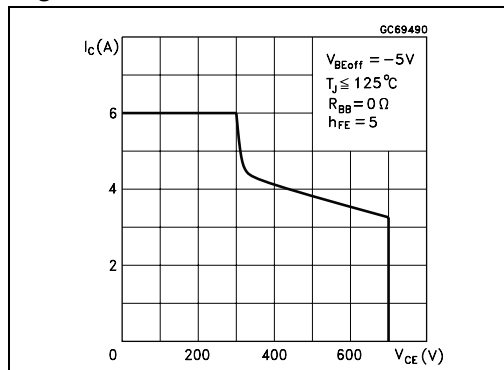
**Figure 10. Resistive load fall time**



**Figure 11. Resistive load storage time**



**Figure 12. Reverse biased SOA**



### 3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

Table 5. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
∅P	3.75		3.85
Q	2.65		2.95



Figure 13. TO-220 type A drawing

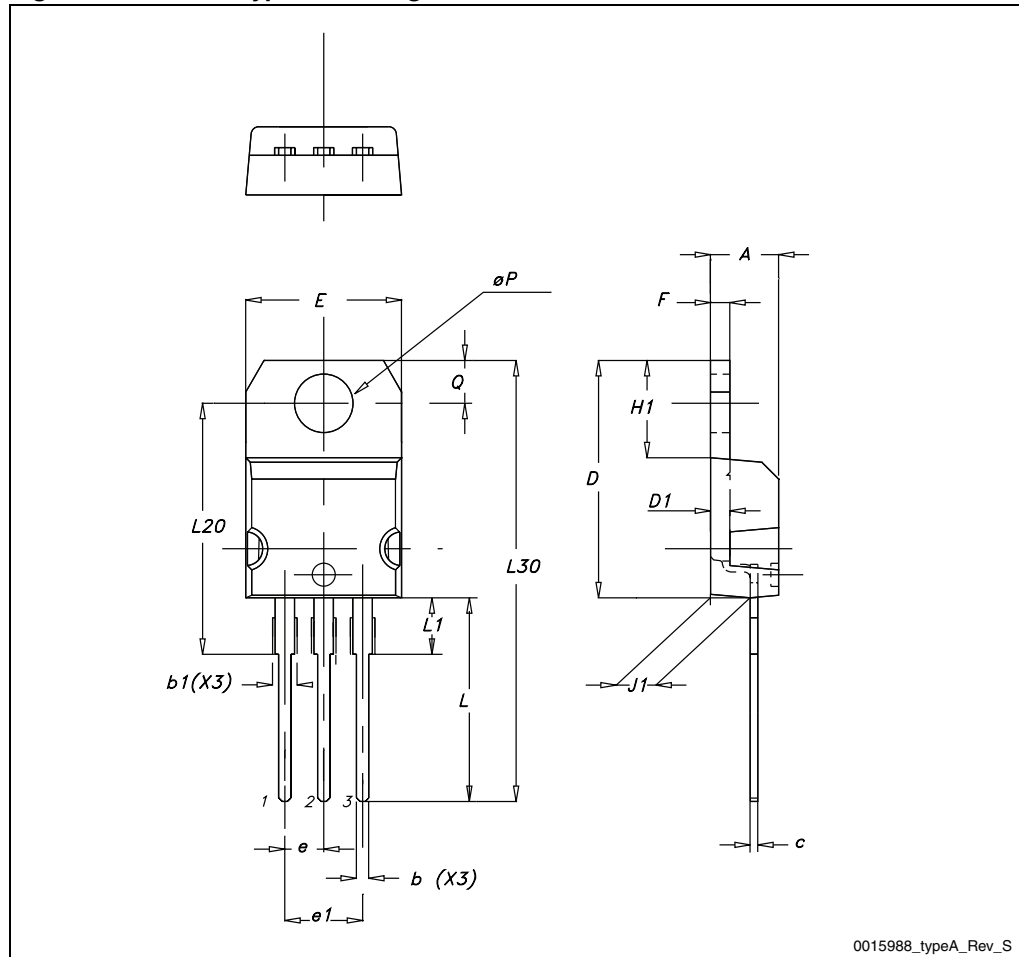
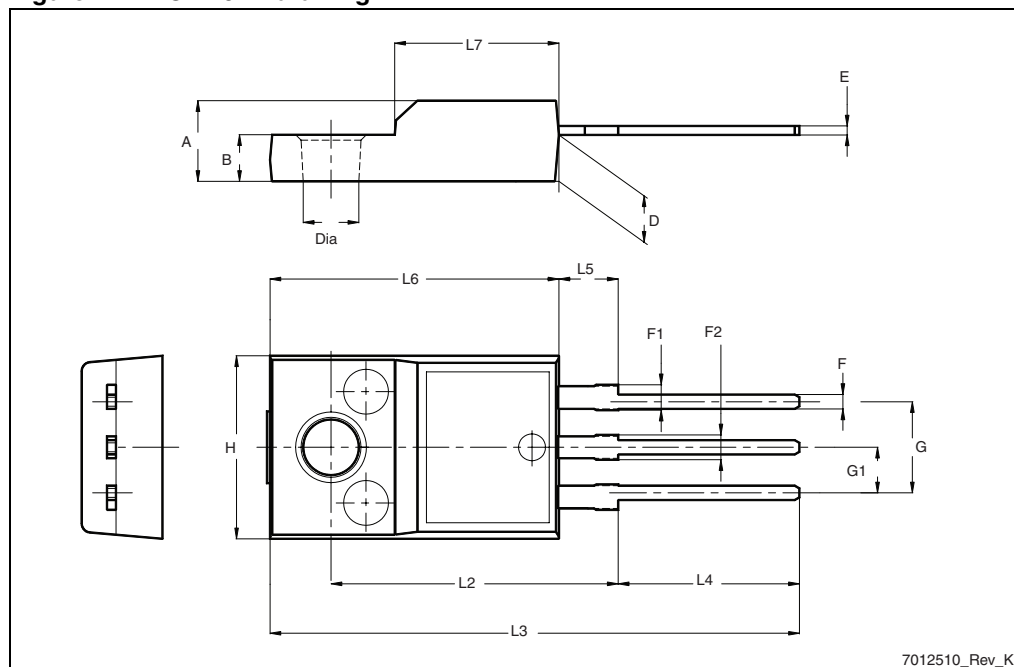


Table 6. TO-220FP mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 14. TO-220FP drawing



## 4 Revision history

Table 7. Document revision history

Date	Revision	Changes
27-Jun-2011	1	First release

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